



### 100V N-CHANNEL ENHANCEMENT MODE MOSFET

### **Product Summary**

BVDSS	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>A</sub> = +25°C
400)/	$225m\Omega$ @ $V_{GS} = 10V$	2.2A
100V	290mΩ @ V <sub>GS</sub> = 4.5V	1.9A

### **Features and Benefits**

- 100% Unclamped Inductive Switch (UIS) Test in Production
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/

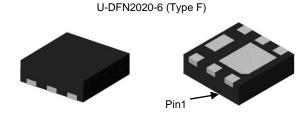
## **Description and Applications**

This new generation MOSFET is designed to minimize the on-state resistance (RDS(ON)) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Load Switch

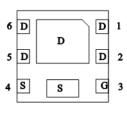
### **Mechanical Data**

- Case: U-DFN2020-6
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.0065 grams (Approximate)

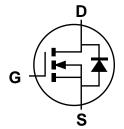


Top View

**Bottom View** 



Pin Out Bottom View



**Equivalent Circuit** 

## **Ordering Information** (Note 4)

Part Number	Case	Quantity Per Reel
DMN10H220LFDF-7	U-DFN2020-6 (Type F)	3,000
DMN10H220LFDF-13	U-DFN2020-6 (Type F)	10,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

# **Marking Information**

U-DFN2020-6 (Type F)



22 = Product Type Marking Code YWX = Date Code Marking Y = Year (ex: 0 = 2020)

W = Week (ex: a = Week 27; z Represents Week 52 and 53)

X = Internal Code (ex: U = Monday)

Date Code Key

Date Code Rey												
Year	2019	2020	2021	2022	2023	2024	2025	2026	2027	2028	2029	2030
Code	G	Н	ı	J	K	L	М	N	0	Р	R	S
Week	1-26				27-52			53				
Code		Α	-Z			а	-z				Z	
Internal Code	Sun	1	Mon	Т	ue	Wed	i	Thu		Fri	;	Sat
Code	Т		U		V	W		Х		Υ		Z



### **Maximum Ratings** (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage		VDSS	100	V
Gate-Source Voltage	V <sub>GSS</sub>	±20	V	
Continuous Drain Current (Note 6) Vgs = 10V	lσ	2.2 1.7	А	
Maximum Body Diode Forward Current (Note 6)	Is	2.2	А	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I <sub>DM</sub>	8.8	Α	
Pulsed Source Current (10µs Pulse, Duty Cycle = 1%)	Ism	8.8	А	
Avalanche Current (Note 9)	las	4.7	А	
Avalanche Energy (Note 9)	Eas	1.1	mJ	

# Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T <sub>A</sub> = +25°C	D-	1.1	W
Total Power Dissipation (Note 5)	$T_A = +70$ °C	PD	0.7	۷V
Thermal Resistance, Junction to Ambient (Note 5)		R <sub>θ</sub> ЈА	110	°C/W
Total Dawar Discination (Note 6)	T <sub>A</sub> = +25°C	Ъ	1.6	W
Total Power Dissipation (Note 6)	T <sub>A</sub> = +70°C	$P_{D}$	1.0	
Thermal Resistance, Junction to Ambient (Note 6)	$R_{\theta JA}$	80	°C/W	
Thermal Resistance, Junction to Case (Note 6)	Rелс	12	C/VV	
Operating and Storage Temperature Range		T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	°C

## **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BVpss	100	_	_	V	V <sub>G</sub> S = 0V, I <sub>D</sub> = 250µA	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	1	μΑ	V <sub>DS</sub> = 100V, V <sub>GS</sub> = 0V	
Gate-Source Leakage	I <sub>GSS</sub>	_	_	100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)	1		I	I	I		
Gate Threshold Voltage	Vgs(TH)	1	_	2.5	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250µA	
Static Drain-Source On-Resistance	_	_	174	225	mΩ	Vgs = 10V, ID = 2A	
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	_	217	290	mΩ	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 1A	
Diode Forward Voltage	VsD	_	0.8	1.3	V	V <sub>G</sub> S = 0V, I <sub>S</sub> = 2A	
DYNAMIC CHARACTERISTICS (Note 8)					•		
Input Capacitance	Ciss	_	384	_		V <sub>DS</sub> = 25V, f = 1MHz, V <sub>GS</sub> = 0V	
Output Capacitance	Coss	_	23	_	pF		
Reverse Transfer Capacitance	Crss	_	17	_			
Gate Resistance	Rg	_	2.4	_	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz	
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Qg	_	3.7	_			
Total Gate Charge (V <sub>GS</sub> = 10V)	Qg	_	6.7	_	nC	V <sub>DD</sub> = 50V, I <sub>D</sub> = 1.6A	
Gate-Source Charge	Qgs	_	1.3	_	IIC		
Gate-Drain Charge	Q <sub>gd</sub>	_	2	_			
Turn-On Delay Time	tD(ON)	_	6.2	_			
Turn-On Rise Time	t <sub>R</sub>	_	8.7	_		V <sub>DD</sub> = 50V, V <sub>GS</sub> = 4.5V,	
Turn-Off Delay Time	tD(OFF)		7.4	_	ns	$R_G = 6.8\Omega$ , $I_D = 1.0A$	
Turn-Off Fall Time	tF		4.2	_			
Body Diode Reverse Recovery Time	t <sub>RR</sub>		20	_	ns	I- 4.4.0 dl/db 4.00.0 ///-	
Body Diode Reverse Recovery Charge	Q <sub>RR</sub>	_	11	_	nC	Is = 1.1A, dl/dt = 100A/µs	

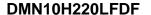
Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

<sup>6.</sup> Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

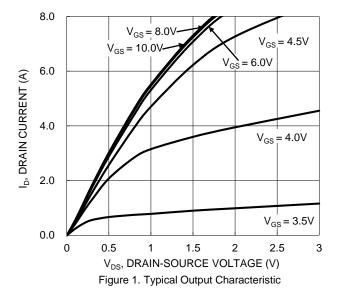
<sup>7.</sup> Short duration pulse test used to minimize self-heating effect.

<sup>8.</sup> Guaranteed by design. Not subject to product testing.

<sup>9.</sup>  $I_{AS}$  and  $E_{AS}$  ratings are based on low frequency and duty cycles to keep  $T_J$  = +25°C.







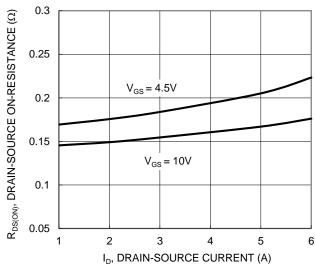


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

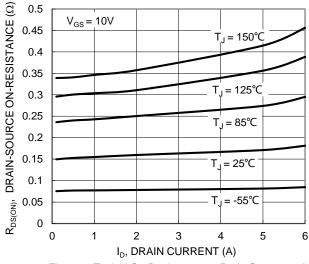


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

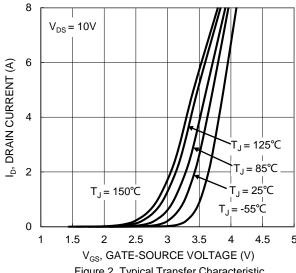


Figure 2. Typical Transfer Characteristic

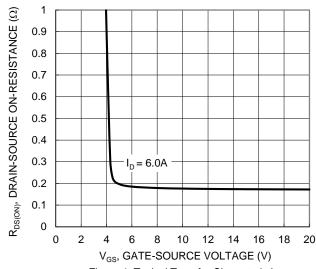


Figure 4. Typical Transfer Characteristic

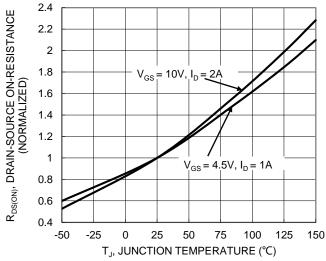


Figure 6. On-Resistance Variation with Junction Temperature





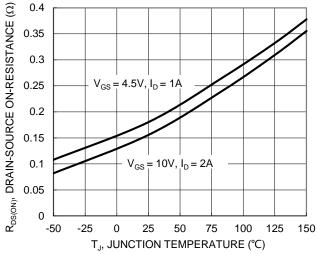


Figure 7. On-Resistance Variation with Junction Temperature

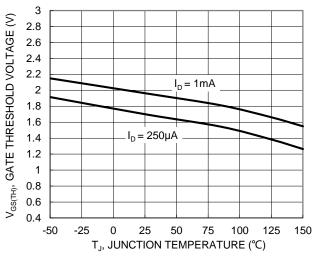


Figure 8. Gate Threshold Variation vs. Junction Temperature

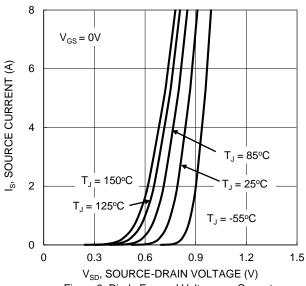
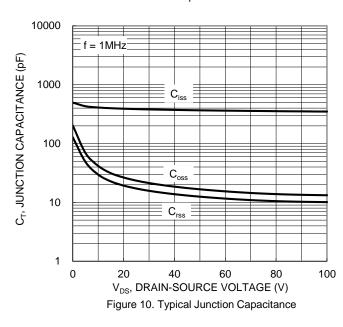
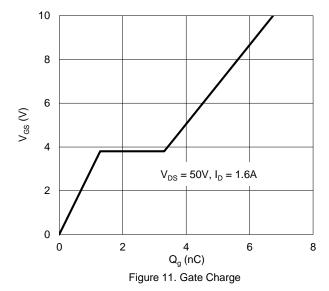


Figure 9. Diode Forward Voltage vs. Current





R<sub>DS(ON)</sub> Limited 10 I<sub>D</sub>, DRAIN CURRENT (A) 1ms = 100µs 1 0.1  $T_{J(Max)} = 150^{\circ}C$   $T_{C} = 25^{\circ}C$ Single Pulse DUT on 1\*MRP 0.01 board  $V_{GS} = 10V$ 0.001 0.1 10 100 1000 V<sub>DS</sub>, DRAIN-SOURCE VOLTAGE (V) Figure 12. SOA, Safe Operation Area

100



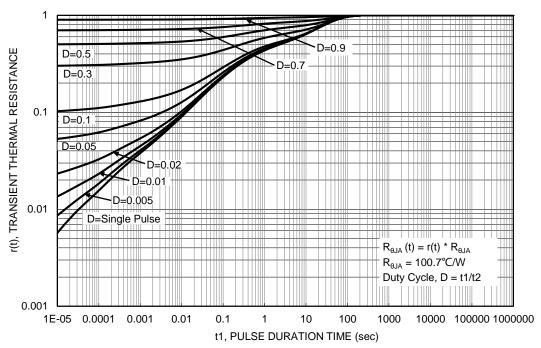


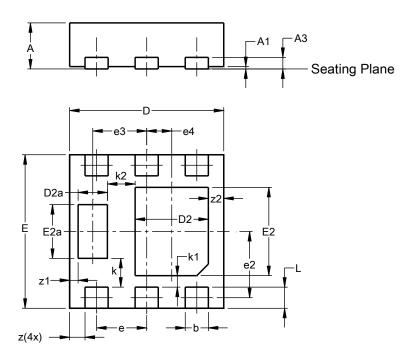
Figure 13. Transient Thermal Resistance



# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### U-DFN2020-6 (Type F)

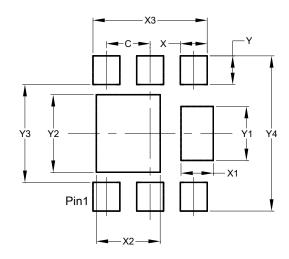


U-DFN2020-6 (Type F)							
Dim	Min Max Typ						
Α	0.57 0.63 0.60						
A1	0.00	0.00 0.05 0.03					
A3	-	-	0.15				
b	0.25	0.35	0.30				
D	1.95	2.05	2.00				
D2	0.85	1.05	0.95				
D2a	0.33	0.43	0.38				
Е	1.95	2.05	2.00				
E2	1.05	1.25	1.15				
E2a	0.65	0.75	0.70				
е	0.65 BSC						
e2	C	0.863 BSC					
е3	(	0.70 BS	С				
e4	0.325 BSC						
k	0.37 BSC						
k1	0.15 BSC						
k2	0.36 BSC						
L	0.225 0.325 0.275						
Z	0.20 BSC						
<b>z</b> 1	0.110 BSC						
z2	0.20 BSC						
All Dimensions in mm							

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### U-DFN2020-6 (Type F)



Dimensions	Value		
Dilliensions	(in mm)		
С	0.650		
X	0.400		
X1	0.480		
X2	0.950		
Х3	1.700		
Y	0.425		
Y1	0.800		
Y2	1.150		
Y3	1.450		
Y4	2.300		



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